

# Tian Pu

## List of Publications by Year in descending order

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10  
papers

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citations

1937685

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1474206

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docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Simulation of a Charged Al <sub>2</sub> O <sub>3</sub> Film as an Assisting Passivation Layer for a-Si Passivated Contact P-Type Silicon Solar Cells. <i>Silicon</i> , 2022, 14, 3339-3348.	3.3	2
2	Enhanced Conversion Efficiency of Monocrystalline P-Type Passivated Emitter and Rear Cells in Commercial Production Line by Improving Rear Side Passivation. <i>Energy Technology</i> , 2021, 9, 2001115.	3.8	0
3	High-efficiency passivated emitter and rear cells with nano honeycomb structure. <i>Solar Energy</i> , 2021, 224, 916-922.	6.1	2
4	Reduced power degradation in bifacial PERC modules by a rear silicon oxide additive layer. <i>International Journal of Energy Research</i> , 2021, 45, 8659-8665.	4.5	2
5	Temperature Effect of Nano-Structure Rebuilding on Removal of DWS mc-Si Marks by Ag/Cu MACE Process and Solar Cell. <i>Energies</i> , 2020, 13, 4890.	3.1	4
6	Improved passivation effect in multicrystalline black silicon by chemical solution pre-treatment. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	2.3	1
7	Nanostructured multi-crystalline silicon solar cell with isotropic etching by HF/KMnO <sub>4</sub> . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600703.	1.8	6
8	High-Efficient Solar Cells by the Ag/Cu-Assisted Chemical Etching Process on Diamond-Wire-Sawn Multicrystalline Silicon. <i>IEEE Journal of Photovoltaics</i> , 2017, 7, 153-156.	2.5	39
9	Hybrid process for texturization of diamond wire sawn multicrystalline silicon solar cell. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 870-873.	2.4	4
10	Efficient light trapping of quasi-inverted nanopyramids in ultrathin c-Si through a cost-effective wet chemical method. <i>RSC Advances</i> , 2016, 6, 96686-96692.	3.6	19